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insulating layer thicker than said first insulating layer on said first insulating layer;

and

wherein a wiring in connection to said circuit electrode is formed on said second insulating layer.

26. A method according to claim 25, wherein said second insulating layer has a thickness of from 35 μm to 150 μm .

27. A method according to claim 25, wherein said second insulating layer has an inclined portion.

28. A method according to claim 27, wherein said inclined portion has an average gradient of from 5 % to 30 %.

29. A method according to claim 25, wherein said second insulating layer is formed by printing with a polyimide paste.

30. A method according to claim 25, wherein said second insulating layer is formed by printing with a resin containing particles therein.

31. A method according to claim 25, wherein said second insulating layer is formed by printing with a thermosetting resin and heating.

32. A method according to claim 25, wherein said second insulating layer is formed by printing and heating.

Claim
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33. A method according to claim 25, wherein said mask used in said printing for formation of the second insulating film has openings smaller than an area of said second insulating layer.

34. A method according to claim 33, wherein said printing for formation of the second insulating film is performed by:

filling a resin into said openings in said mask by moving a squeegee on said mask; and
separating said mask from said wafer.

35. A method according to claim 25, further comprising the step of forming an external connection terminal connected to said wiring.

36. A method according to claim 25, further comprising the step of forming a third electrically insulating layer covering said second insulating layer and said wiring.

37. A method according to claim 25, further comprising the step of forming a surface protective layer covering said second insulating layer and said wiring.

38. A method according to claim 25, further comprising the step of dicing said wafer. --